

Data sheet acquired from Harris Semiconductor SCHS189

January 1998

High Speed CMOS Logic Octal Buffer and Line Drivers, Three-State

#### Features

- CD74HC540, CD74HCT540 . . . . . Inverting
- CD74HC541, CD74HCT541 .....Non-Inverting
- Buffered Inputs
- Three-State Outputs
- . Bus Line Driving Capability
- Typical Propagation Delay = 9ns at V<sub>CC</sub> = 5V,
   C<sub>L</sub> = 15pF, T<sub>A</sub> = 25°C
- Fanout (Over Temperature Range)
  - Standard Outputs...... 10 LSTTL Loads
  - Bus Driver Outputs ........... 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
  - 2V to 6V Operation
  - High Noise Immunity:  $N_{IL}$  = 30%,  $N_{IH}$  = 30% of  $V_{CC}$  at  $V_{CC}$  = 5V
- HCT Types
  - 4.5V to 5.5V Operation
  - Direct LSTTL Input Logic Compatibility,
     V<sub>IL</sub>= 0.8V (Max), V<sub>IH</sub> = 2V (Min)

CD74HC540, CD74HCT540

(PDIP, SOIC)

## Description

The Harris CD74HC540 and CD74HCT540 are Inverting Octal Buffers and Line Drivers with Three-State Outputs and the capability to drive 15 LSTTL loads. The Harris CD74HC541 and CD74HCT541 are Non-Inverting Octal Buffers and Line Drivers with Three-State Outputs that can drive 15 LSTTL loads. The Output Enables  $(\overline{OE1})$  and  $(\overline{OE2})$  control the Three-State Outputs. If either  $\overline{OE1}$  or  $\overline{OE2}$  is HIGH the outputs will be in the high impedance state. For data output  $\overline{OE1}$  and  $\overline{OE2}$  both must be LOW.

## **Ordering Information**

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CD74HC540E	-55 to 125	20 Ld PDIP	E20.3
CD74HCT540E	-55 to 125	20 Ld PDIP	E20.3
CD74HC541E	-55 to 125	20 Ld PDIP	E20.3
CD74HCT541E	-55 to 125	20 Ld PDIP	E20.3
CD74HC540M	-55 to 125	20 Ld SOIC	M20.3
CD74HCT540M	-55 to 125	20 Ld SOIC	M20.3
CD74HC541M	-55 to 125	20 Ld SOIC	M20.3
CD74HCT541M	-55 to 125	20 Ld SOIC	M20.3

#### NOTES:

- 1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
- Wafer and die for this part number is available which meets all electrical specifications. Please contact your local sales office or Harris customer service for ordering information.

### **Pinouts**

TOP VIEW OE 1 20 V<sub>CC</sub> 19 OE2 A0 2 A1 3 Y0 Α2 16  $\overline{\mathbf{Y2}}$ A3 15 Y3 Α4 14 Y4 A5 7 13 <u>75</u> Α6 12 Y6 Α7

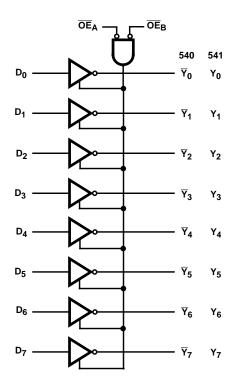
GND 10

CD74HC541, CD74HCT541 (PDIP, SOIC) TOP VIEW

OE1	1		20	v <sub>cc</sub>
A0	2		19	OE2
<b>A</b> 1	3		18	Y0
A2	4		17	<b>Y1</b>
А3	5		16	Y2
<b>A4</b>	6		15	<b>Y3</b>
Α5	7		14	Y4
Α6	8		13	Y5
Α7	9		12	Y6
GND	10		11	Y7

11 Y7

# Functional Diagram



#### **TRUTH TABLE**

	INPUTS	OUTPUTS				
OE1	OE2	An	540	541		
L	L	Н	L	Н		
Н	Х	Х	Z	Z		
Х	Н	Х	Z	Z		
L	L	L	Н	L		

#### NOTE:

H = HIGH Voltage Level
L = LOW Voltage Level

X = Don't Care

Z = High Impedance

### **Absolute Maximum Ratings**

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#### **Thermal Information**

Thermal Resistance (Typical, Note 3)	$\theta_{JA}$ (oC/W)
PDIP Package	. 125
SOIC Package	. 120
Maximum Junction Temperature	150 <sup>0</sup> C
Maximum Storage Temperature Range	-65°C to 150°C
Maximum Lead Temperature (Soldering 10s)	300°C
(SOIC - Lead Tips Only)	

### **Operating Conditions**

Temperature Range, T <sub>A</sub> 55°C to 125°C Supply Voltage Range, V <sub>CC</sub>
117 0 0 0
HC Types
HCT Types
DC Input or Output Voltage, V <sub>I</sub> , V <sub>O</sub> 0V to V <sub>CC</sub>
Input Rise and Fall Time
2V
4.5V 500ns (Max)
6V

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

#### NOTE:

3.  $\theta_{JA}$  is measured with the component mounted on an evaluation PC board in free air.

# **DC Electrical Specifications**

		TEST CONDITIONS		V <sub>CC</sub>	25°C			-40°C 1	O 85°C	-55°C TO 125°C		
PARAMETER	SYMBOL	V <sub>I</sub> (V)	I <sub>O</sub> (mA)	(S)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
HC TYPES					-	-	-	-				
High Level Input	V <sub>IH</sub>	-	-	2	1.5	-	-	1.5	-	1.5	-	V
Voltage				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input	V <sub>IL</sub>	-	-	2	-	-	0.5	-	0.5	-	0.5	V
Voltage				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output	VoH	V <sub>IH</sub> or V <sub>IL</sub>	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
Voltage CMOS Loads			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
omeo Edudo			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output	7		-	-	-	-	-	-	-	-	-	V
Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
112 20000			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output	V <sub>OL</sub>	V <sub>IH</sub> or V <sub>IL</sub>	0.02	2	-	-	0.1	-	0.1	-	0.1	V
Voltage CMOS Loads			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
omeo Edudo			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output	7		-	-	-	-	-	-	-	-	-	V
Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	II	V <sub>CC</sub> or GND	-	6	-	-	±0.1	-	±1	-	±1	μА

# DC Electrical Specifications (Continued)

		TEST CONDITIONS		V <sub>CC</sub>	25°C			-40°C 1	TO 85°C	-55°C TO 125°C		
PARAMETER	SYMBOL	V <sub>I</sub> (V)	I <sub>O</sub> (mA)	(V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
Quiescent Device Current	Icc	V <sub>CC</sub> or GND	0	6	-	-	8	-	80	-	160	μΑ
Three- State Leakage Current	l <sub>OZ</sub>	V <sub>IL</sub> or V <sub>IH</sub>	V <sub>O</sub> = V <sub>CC</sub> or GND	6	-	-	±0.5	-	±5.0	-	±10	μА
HCT TYPES	•	•	•				•	•	•	•		
High Level Input Voltage	V <sub>IH</sub>	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V <sub>IL</sub>	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V <sub>ОН</sub>	V <sub>IH</sub> or V <sub>IL</sub>	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V <sub>OL</sub>	V <sub>IH</sub> or V <sub>IL</sub>	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	lį	V <sub>CC</sub> and GND	0	5.5	-		±0.1	-	±1	-	±1	μА
Quiescent Device Current	Icc	V <sub>CC</sub> or GND	0	5.5	-	-	8	-	80	-	160	μА
Three- State Leakage Current	l <sub>OZ</sub>	V <sub>IL</sub> or V <sub>IH</sub>	V <sub>O</sub> = V <sub>CC</sub> or GND	5.5	-	-	±0.5	-	±5.0	-	±10	μА
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	Δl <sub>CC</sub>	V <sub>CC</sub> -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μА

NOTE: For dual-supply systems theoretical worst case ( $V_I = 2.4V$ ,  $V_{CC} = 5.5V$ ) specification is 1.8mA.

# **HCT Input Loading Table**

	UNIT LOADS							
INPUT	HCT540	HCT541						
A0 - A7	1	0.4						
OE2	0.75	0.75						
OE1	1.15	1.15						

NOTE: Unit load is  $\Delta I_{CC}$  limit specific in DC Electrical Specifications Table, e.g., 360µA max. at 25°C.

**Switching Specifications**  $C_L = 50pF$ , Input  $t_r$ ,  $t_f = 6ns$ 

		TEST			25°C			°С ОТ О		C TO 5°C	UNITS
PARAMETER	SYMBOL	CONDITIONS	V <sub>CC</sub> (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES										•	
Propagation Delay Data to Outputs (540)	t <sub>PLH</sub> , t <sub>PHL</sub>	$C_L = 50pF$	2	-	-	110	-	140	-	165	ns
			4.5	-	-	22	-	28	-	33	ns
		C <sub>L</sub> = 15pF	5	-	9	-	-	-	-	-	ns
		C <sub>L</sub> = 50pF	6	-	-	19	-	24	-	28	ns
Data to Outputs (541)	t <sub>PLZ</sub> , t <sub>PHZ</sub>	C <sub>L</sub> = 50pF	2	-	-	115	-	145	-	175	ns
			4.5	-	-	23	-	29	-	35	ns
		C <sub>L</sub> = 15pF	5	-	9	-	-	-	-	-	ns
		C <sub>L</sub> = 50pF	6	-	-	20	-	25	-	30	ns
Output Enable and Disable	t <sub>PLZ</sub> , t <sub>PHZ</sub>	C <sub>L</sub> = 50pF	2	-	-	160	-	200	-	240	ns
to Outputs (540)			4.5	-	-	32	-	40	-	48	ns
		C <sub>L</sub> = 15pF	5	-	13	-	-	-	-	-	ns
		C <sub>L</sub> = 50pF	6	-	-	27	-	34	-	41	ns
Output Enable and Disable	t <sub>PLZ</sub> , t <sub>PHZ</sub>	C <sub>L</sub> = 50pF	2	-	-	160	-	200	-	240	ns
to Outputs (541)			4.5	-	-	32	-	40	-	48	ns
		C <sub>L</sub> = 15pF	5	-	14	-	-	-	-	-	ns
		C <sub>L</sub> = 50pF	6	-	-	23	-	29	-	35	ns
Output Transition Time	t <sub>THL</sub> , t <sub>TLH</sub>	C <sub>L</sub> = 50pF	2	-	-	60	-	75	-	90	ns
			4.5	-	-	12	-	15	-	18	ns
			6	-	-	10	-	13	-	15	ns
Input Capacitance	C <sub>I</sub>	C <sub>L</sub> = 50pF	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	co	-	-	20	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 4, 5) (540)	C <sub>PD</sub>	C <sub>L</sub> = 15pF	5	-	50	-	-	-	-	-	pF
Power Dissipation Capacitance (Notes 4, 5) (541)	C <sub>PD</sub>	C <sub>L</sub> = 15pF	5	-	48	-	-	-	-	-	pF
HCT TYPES										•	
Propagation Delay	t <sub>PHL</sub> , t <sub>PLH</sub>										
Data to Outputs (540)		C <sub>L</sub> = 50pF	4.5	-	-	24	-	30	-	36	ns
		C <sub>L</sub> = 15pF	5	-	9	-	-	-	-	-	ns
Data to Outputs (541)	t <sub>PHL</sub> , t <sub>PLH</sub>	C <sub>L</sub> = 50pF	4.5	-	-	28	-	35	-	42	ns
		$C_L = 15pF$	5	-	11	-	-	-	-	-	ns
Output Enable and Disable to Outputs (540, 541)	t <sub>PLZ</sub> , t <sub>PHZ</sub>	C <sub>L</sub> = 50pF	4.5	-	-	35	-	44	1	53	ns
Outputs (040, 041)		$C_L = 15pF$	5	-	14	1	1	-	1	-	ns
Output Transition Time	t <sub>TLH</sub> , t <sub>THL</sub>	C <sub>L</sub> = 50pF	4.5	-	-	12	-	15	-	18	ns
Input Capacitance	C <sub>I</sub>	C <sub>L</sub> = 50pF	-	10	-	10	-	10	-	10	pF

# Switching Specifications $C_L = 50pF$ , Input $t_r$ , $t_f = 6ns$ (Continued)

		TEST		25°C		-40°C TO -55°C T 25°C 85°C 125°C					
PARAMETER	SYMBOL	CONDITIONS	V <sub>CC</sub> (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
Three-State Output Capacitance	CO	-	-	20	-	20	i	20	-	20	pF
Power Dissipation Capacitance (Notes 4, 5) (540, 541)	C <sub>PD</sub>	C <sub>L</sub> = 15pF	5	ı	55	-	ī	-	-	-	pF

#### NOTES:

- 4. C<sub>PD</sub> is used to determine the dynamic power consumption, per channel.
- 5.  $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$  where  $f_i = Input$  Frequency,  $C_L = Output$  Load Capacitance,  $V_{CC} = Supply$  Voltage.

### Test Circuits and Waveforms

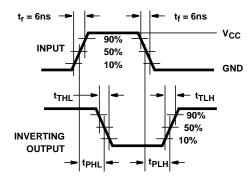


FIGURE 1. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

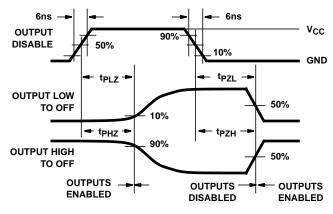


FIGURE 3. HC THREE-STATE PROPAGATION DELAY WAVEFORM

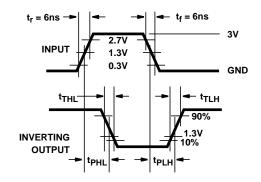


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

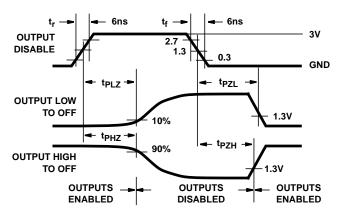
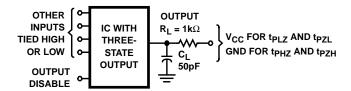


FIGURE 4. HCT THREE-STATE PROPAGATION DELAY WAVEFORM

# Test Circuits and Waveforms (Continued)



NOTE: Open drain waveforms  $t_{PLZ}$  and  $t_{PZL}$  are the same as those for three-state shown on the left. The test circuit is Output  $R_L = 1k\Omega$  to  $V_{CC}$ ,  $C_L = 50pF$ .

FIGURE 5. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT

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